

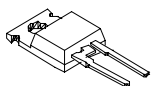
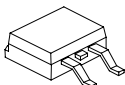
MBR735-G/ MBR745-G/ MBRB735-G/MBRB745-G
SCHOTTKY RECTIFIER

Applications:

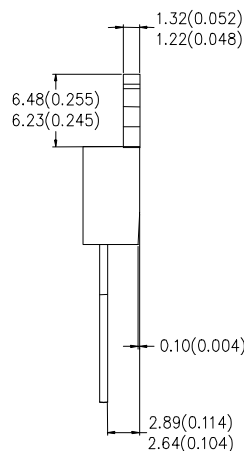
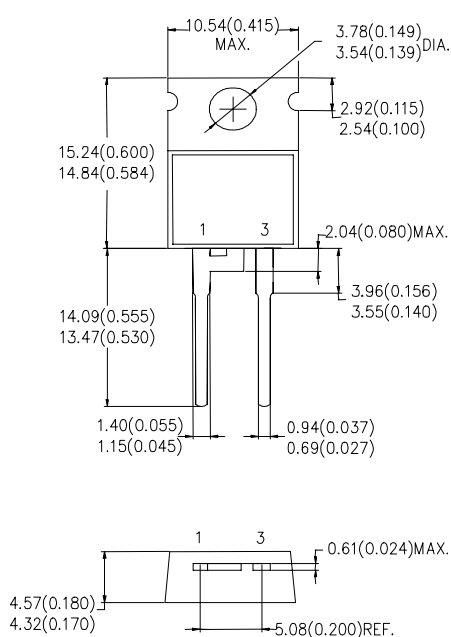
- Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

Features:

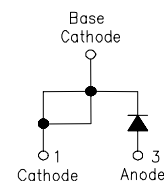
- 150 °C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green Products in Compliance with the RoHS Directive

| Case styles | |
|--|--|
| MBR735-G/MBR745-G  TO-220AC | MBRB735-G/MBRB745-G  D²PAK |

Mechanical Dimensions: In Inches / mm

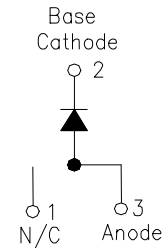
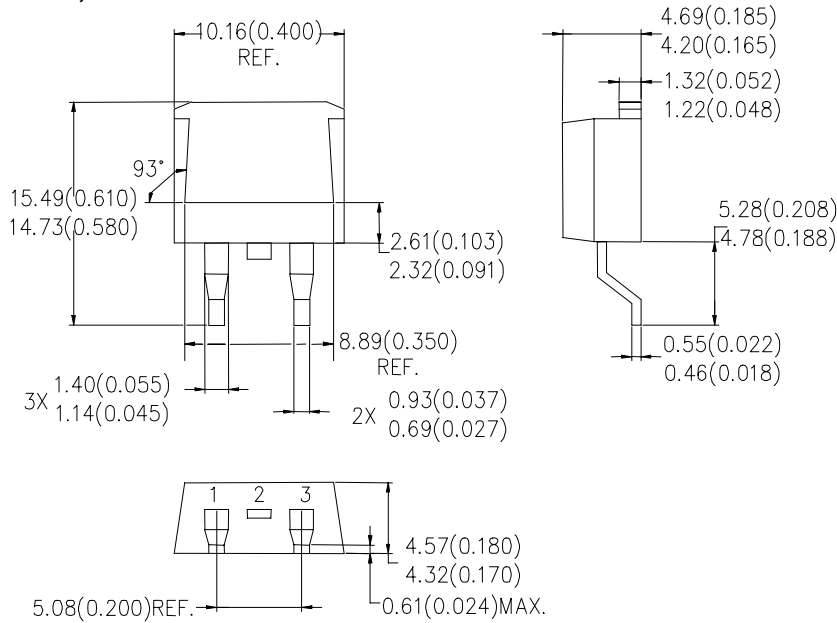


TO-220AC



Data Sheet 3415, Rev. -

Green Products
D²PAK



Maximum Ratings:

| Characteristics | Symbol | Condition | Max. | Units |
|--|-------------|--|--------------------------------|-------|
| Peak Inverse Voltage | V_{RWM} | - | 35(MBR.735-G) 45(MBR.745-G) | V |
| Max. Average Forward Current | $I_{F(AV)}$ | @ $T_C = 131^\circ\text{C}$ (Rated V_R) | 7.5 | A |
| Max. Peak One Cycle Non-Repetitive Surge Current | I_{FSM} | 8.3 ms, half Sine pulse | 150 | A |
| Peak Repetitive Reverse Surge Current | I_{RRM} | 2.0 μsec 1.0 KHz | 1.0 | A |

Electrical Characteristics:

| Characteristics | Symbol | Condition | Max. | Units |
|--|----------|---|--------------|------------------|
| Max. Forward Voltage Drop * | V_{F1} | @15 A, Pulse, $T_J = 25^\circ\text{C}$ | 0.84 | V |
| | V_{F2} | @7.5 A, Pulse, $T_J = 125^\circ\text{C}$ @15 A, Pulse, $T_J = 125^\circ\text{C}$ | 0.57 0.72 | V |
| Max. Reverse Current * | I_{R1} | @ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25^\circ\text{C}$ | 0.1 | mA |
| | I_{R2} | @ $V_R = \text{Rated } V_R$, Pulse, $T_J = 125^\circ\text{C}$ | 15.0 | mA |
| Max. Junction Capacitance | C_T | @ $V_R = 5\text{ V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$ | 400 | pF |
| Typical Series Inductance | L_S | Measured lead to lead 5 mm from package body | 8.0 | nH |
| Max. Voltage Rate of Change (Rated V_R) | dv/dt | - | 10,00 | V/ μs |

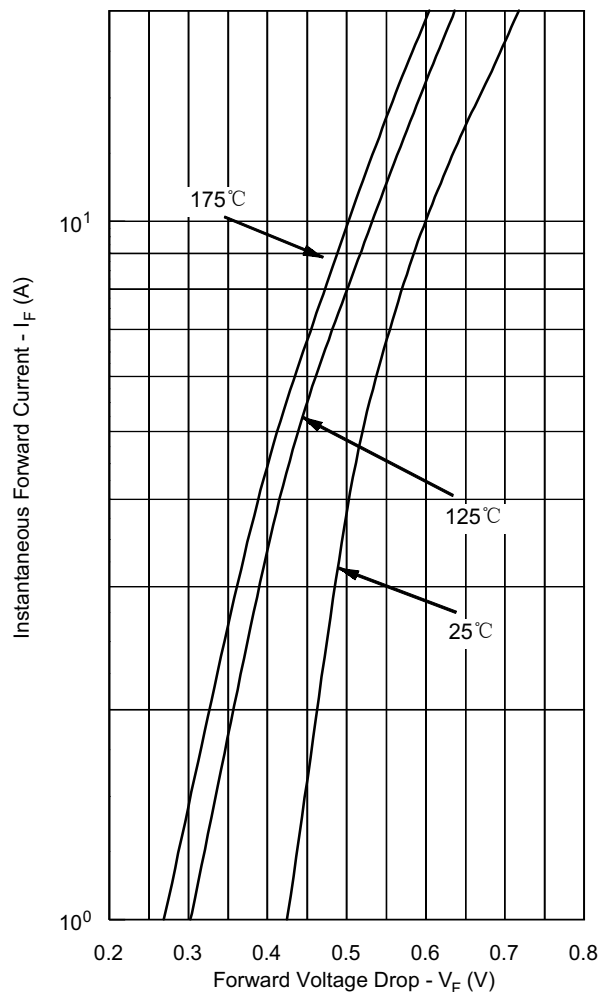
* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications:

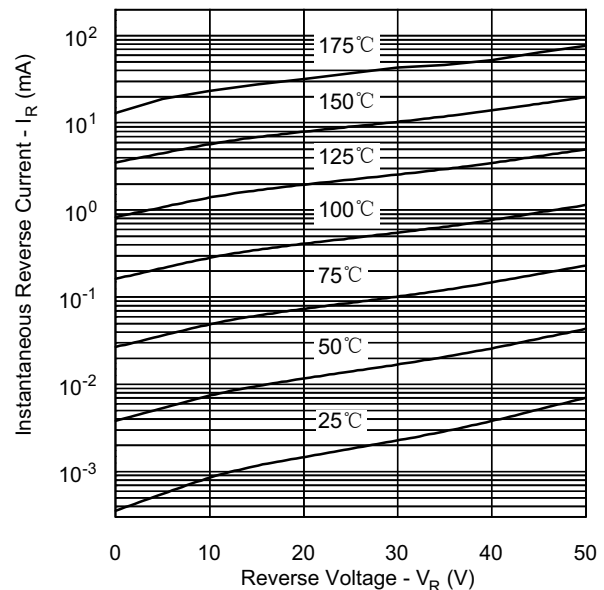
- 221 West Industry Court ■ Deer Park, NY 11729-4681 ■ (631) 586-7600 FAX (631) 242-9798 •
- World Wide Web Site - <http://www.sensitron.com> • E-Mail Address - sales@sensitron.com •

| Characteristics | Symbol | Condition | Specification | Units |
|---|---|--------------------------------------|---------------------|-------|
| Max. Junction Temperature | T_J | - | -65 to +150 | °C |
| Max. Storage Temperature | T_{stg} | - | -65 to +175 | °C |
| Maximum Thermal Resistance Junction to Case | $R_{\theta JC}$ | DC operation | 3.0 | °C/W |
| Typical Thermal Resistance, Case to Heat Sink | $R_{\theta CS}$ | Mounting surface, smooth and greased | 0.50 | °C/W |
| Approximate Weight | wt | - | 2 | g |
| Mounting Torque | T_M | - | 6 (min) 12 (max) | Kg-cm |
| Case Style | TO-220AC D ² PAK (Suffix "s" for D ² PAK; "MBRB xxxx" for D ² PAK) | | | |

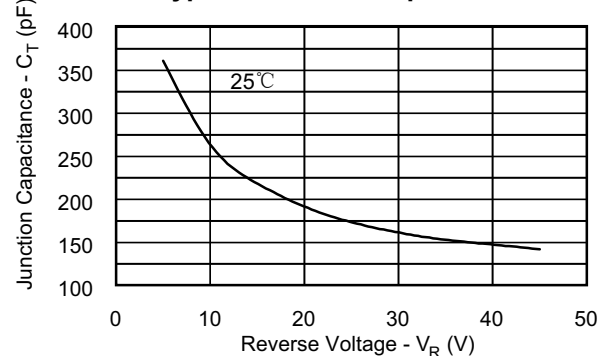
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.